

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI MLN1033S** is Designed for

FEATURES:

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-
- **Omnigold™** Metalization System

MAXIMUM RATINGS

| | |
|-------------------------|--------------------------------|
| I_C | 10 A |
| V_{CB} | 60 V |
| V_{CE} | 35 V |
| P_{DISS} | 140 W @ T _C = 25 °C |
| T_J | -65 °C to +200 °C |
| T_{STG} | -65 °C to +150 °C |
| θ_{JC} | 17 °C/W |

PACKAGE STYLE .280 4L STUD

| DIM | MINIMUM inches / mm | MAXIMUM inches / mm |
|-----|------------------------|------------------------|
| A | 1.010 / 25.65 | 1.055 / 26.80 |
| B | .220 / 5.59 | .230 / 5.84 |
| C | .270 / 6.86 | .285 / 7.24 |
| D | .003 / 0.08 | .007 / 0.18 |
| E | .117 / 2.97 | .137 / 3.48 |
| F | .572 / 14.53 | |
| G | .130 / 3.30 | |
| H | .245 / 6.22 | .255 / 6.48 |
| I | .640 / 16.26 | |
| J | .175 / 4.45 | .217 / 5.51 |
| K | .275 / 6.99 | .285 / 7.24 |

ORDER CODE: ASI10627

CHARACTERISTICS T_C = 25 °C

| SYMBOL | TEST CONDITIONS | MINIMUM | TYPICAL | MAXIMUM | UNITS |
|-------------------------|---|---------|---------|---------|------------|
| BV_{CEO} | I _C = 50 mA | 35 | | | V |
| BV_{CER} | I _C = 50 mA R _{BE} = 10 Ω | 60 | | | V |
| BV_{EBO} | I _E = 10 mA | 4.0 | | | V |
| I_{CES} | V _E = 28 V | | | 5 | mA |
| h_{FE} | V _{CE} = 5.0 V I _C = 1.0 A | 10 | | 100 | --- |
| C_{ob} | V _{CB} = 28 V f = 1.0 MHz | | | 5.5 | pF |
| P_G | V _{CE} = 18 V I _{CQ} = 220 mA f = 1.0 GHz P _{OUT} = 2.0 W | 9.0 | | | dB |